

EAST - [usinfo.wsp.1]

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Drafts

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L1: (15) "5911114"

L2: (17) "6171959"

L3: (2) "6335294"

L4: (3) "6329276"

L5: (7) (("5911114") or ("6171959") or ("6335294") or ("6329276"))

L6: (2990) cobalt adj silicide

L7: (25) 6 and (titanium adj rich)

L8: (0) 5 and (titanium adj rich)

L9: (120) silicide and (titanium adj rich)

L10: (110) 9 and anneal\$3

L11: (20) 10 and (silicide.clm. or (titanium adj rich).clm.)

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(0) ("(thinadjfilm)nearresistor").PN.

(0) ("(thinadjfilm)nearresistor").PN.

(150130) thin adj film

(14857) (thin adj film) and resistor

(2054) ((thin adj film) and resistor) and ((thin adj film) and resistor) and ((thin adj film) and resistor)

USPAT:US6318

Details: 00

P High Definition

10 and (silicide.clm. or (titanium adj rich).clm.)

Advanced

Advanced

Group

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	U	T	PT	P	Document ID	Issue Dat	Pages	Title	Current OF	Current XR	Retrieval	Inventor	S	C	T	W	W
53	P	P	P	P	US 6054386	20000425	10	Process for forming silicon-on-insulator de	438/682	257/E21.16		Prabhakar, Venkatraman	P	P	P	P	P
54	P	P	P	P	US 6013569	20000111	10	One step silicide process without bridging	438/595	257/288;		Lur, Water et al.	C	P	P	P	P
57	P	P	P	P	US 5981383	19991109	11	Method of fabricating a silicide layer of a dev	438/655	257/E21.16		Lur, Water et al.	P	P	P	P	P
58	P	P	P	P	US 5972790	19991026	10	Method for forming silicides	438/649	257/E21.16		Arena, Chantal et al.	P	P	P	P	P
59	P	P	P	P	US 5863393	19990126	10	Low angle, low energy physical vapor depositi	204/192.3	204/192.12		Hu, Yongjun	C	P	P	P	P
60	P	P	P	P	US 5807770	19980915	17	Fabrication method of semiconductor device co	438/151	257/E21.16		Mineji, Akira	C	P	P	P	P
61	P	P	P	P	US 5741725	19980421	15	Fabrication process for semiconductor device ha	438/664	257/E21.16		Inoue, Ken et al.	P	P	P	P	P
62	P	P	P	P	US 5741721	19980421	17	Method of forming capacitors and intercon	438/396	257/E21.00		Stevens, E. Henry	C	P	P	P	P
63	P	P	P	P	US 5725739	19980310	10	Low angle, low energy physical vapor depositi	204/192.3	204/192.17		Hu, Yongjun	P	P	P	P	P
64	P	P	P	P	US 5508881	19960416	21	Capacitors and interconnect lines for	361/305	257/532;		Stevens, E. Henry	C	P	P	P	P
65	P	P	P	P	US 4931411	19900605	12	Integrated circuit process with TiN-gate t	438/201	148/DIG.11		Tigelaar, Howard L. et al.	C	P	P	P	P
66	P	P	P	P	US 4894693	19900116	12	Single-polysilicon dram	257/311	257/384;		Tigelaar, Howard	C	P	P	P	P

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